

QUAD INVERTING TRANSISTOR SWITCH

1 FEATURES

- OUTPUT VOLTAGE TO 50V
- OUTPUT CURRENT TO 1.2A
- VERY LOW SATURATION VOLTAGE
- TTL COMPATIBLE INPUTS
- INTEGRAL SUPPRESSION DIODE

2 DESCRIPTION

The L9222 monolithic quad transistor switch is designed for high current, high voltage switching applications.

Each of the four switches is controlled by a logic input and all four are controlled by a common enable input. All inputs are TTL-compatible for direct connection to logic circuits. Each switch consists of an open-collector transistor plus a clamp diode for applications with inductive loads.

Figure 1. Packages

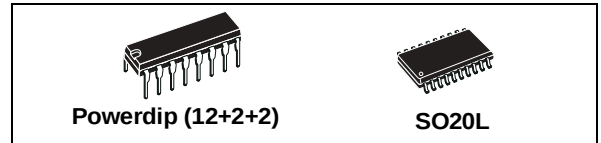


Table 1. Order Codes

Part Number	Package
L9222	(PDIP12+2+2)
L9222 D	(SO20L)

The emitters of the four switches are connected together to GND. The switches of the same device may be paralld. The device is intended to drive coils such as relays, solenoids, unipolar stepper motors, LED etc.

Figure 2. BLOCK DIAGRAM

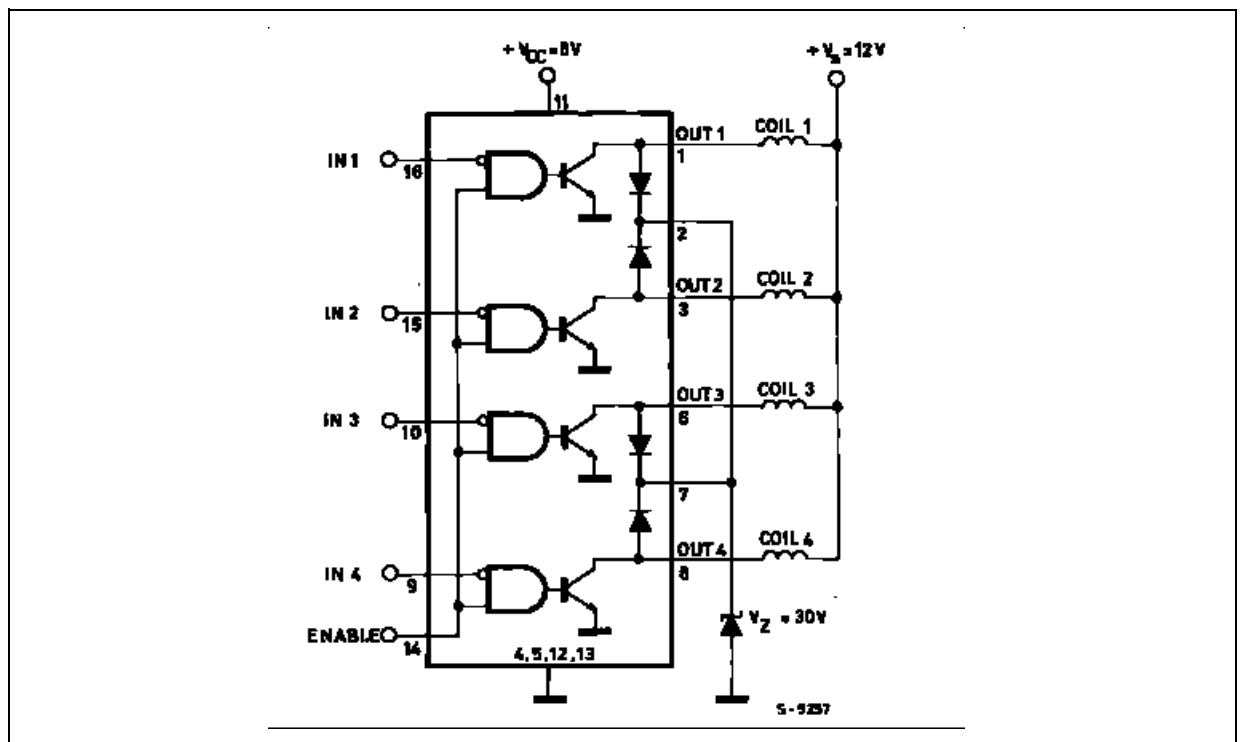


Table 2. ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{OUT}	Output Voltage	- 0.7 to 50	V
V_{CC}	Logic Supply Voltage	7	V
V_i	Input Voltage	- 0.7 to $V_{CC} + 0.3$	V
T_j, T_{ST}	Junction and Storage Temperature Range	- 55 to 150	°C

Figure 3. PIN CONNECTION (Top view)

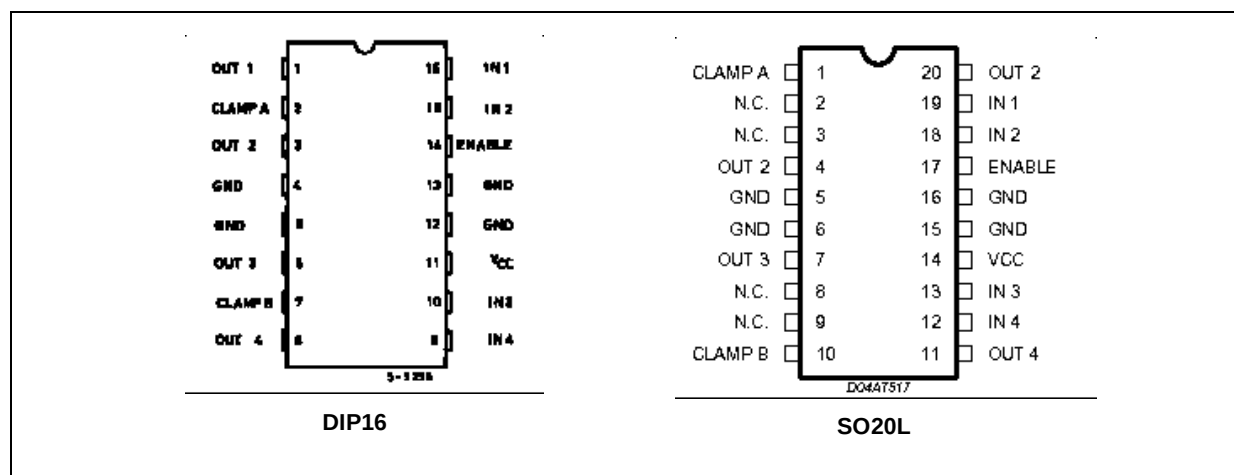


Table 3. TRUTH TABLE

Enable	Input	Power Out
H	L	ON
H	H	OFF
L	X	OFF

For each input :

H= High level

L= Low level

X = Don't care

Table 4. THERMAL DATA

Symbol	Parameter	Value	Unit
$R_{th j-amb}$	Thermal Resistance Junction to ambient	Max 90	°C/W
$R_{th j-case}$	Thermal Resistance Junction to case	Max 14	°C/W

Table 5. ELECTRICAL CHARACTERISTICS

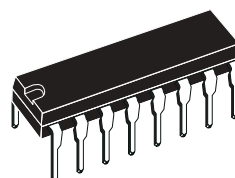
$V_{CC} = 5V_{dc} \pm 5\%$ $V_{EN} = 5V - 40 \leq T_j \leq 125^\circ C$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{CE(sus)}$	Output Sustaining Voltage	$V_{IN} = 2V$ $V_{EN} = 2V$, $I_{OUT} = 100mA$	46			V
I_{CEX}	Output Leakage Current	$V_{CE} = 50V$ $V_{IN} = 2V$, $V_{EN} = 0.8V$			1	mA
$V_{CE(sat)}$	Collector Emitter Saturation	$V_{IN} \geq 0.8V$ $I_{OUT} = 0.1A$ $I_{OUT} = 0.3A$ $I_{OUT} = 0.6A$; $-40 + 105^\circ C$			0.3 0.5 0.8	V V V
V_{IL}	Input Low Voltage				0.8	V
I_{IL}	Input Low Current	$V_{IN} = 0.4V$	- 15			μA
V_{IH}	Input High Voltage		2.0			V
I_{IH}	Input High Current	$V_{IN} \geq 2.0V$	- 15			μA
I_S	Logic Supply Current	All Outputs ON $I_{OUT} = 06A$		50	90	mA
		All Outputs OFF		10	20	mA
I_R	Clamp Diode Leakage Current	$V_R = 50V$ Diode Reverse Voltage			100	μA
V_F	Clamp Diode Forward Voltage	$I_F = 0.6A$			1.8	V
		$I_F = 1.2A$			2.0	V
I_{OUT}	Output Current	$V_{IN} = 0.4V$, $R = 10\Omega$, $V_S = 13V$	0.9	1.2		A
T_{PHL}	Propagation Delay Time (high to low transition)	$T_j = 25^\circ C$ $I_L = 600mA$			20	μs
T_{PHL}	Propagation Delay Time (low to high transition)	$I_L = 600mA$ $T_j = 25^\circ C$			20	μs
V_{ENL}	Low Enable Voltage				0.8	V
I_{ENL}	Low Enable Current	$V_{EN} = 0.4V$	- 15			μA
V_{ENH}	High Enable Voltage		2.0			V
I_{ENH}	High Enable Current	$V_{EN} \geq 2.0V$	- 15		15	μA

Figure 4. Powerdip (12+2+2) Mechanical Data & Package Dimensions

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.85		1.40	0.033		0.055
b		0.50			0.020	
b1	0.38		0.50	0.015		0.020
D			20.0			0.787
E		8.80			0.346	
e		2.54			0.100	
e3		17.78			0.700	
F			7.10			0.280
I			5.10			0.201
L		3.30			0.130	
Z			1.27			0.050

OUTLINE AND MECHANICAL DATA



Powerdip 16

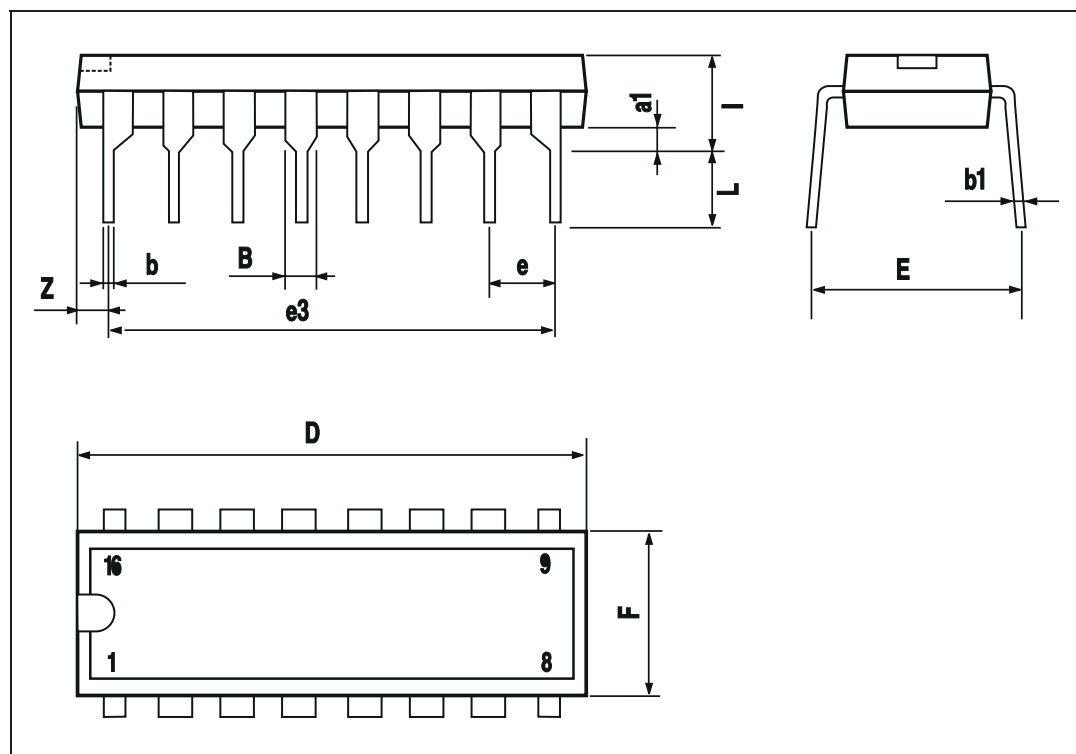
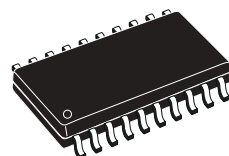


Figure 5. SO20L Mechanical Data & Package Dimensions

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.35		2.65	0.093		0.104
A1	0.10		0.30	0.004		0.012
B	0.33		0.51	0.013		0.200
C	0.23		0.32	0.009		0.013
D ⁽¹⁾	12.60		13.00	0.496		0.512
E	7.40		7.60	0.291		0.299
e		1.27			0.050	
H	10.0		10.65	0.394		0.419
h	0.25		0.75	0.010		0.030
L	0.40		1.27	0.016		0.050
k	0° (min.), 8° (max.)					
ddd			0.10			0.004

(1) "D" dimension does not include mold flash, protusions or gate burrs. Mold flash, protusions or gate burrs shall not exceed 0.15mm per side.

OUTLINE AND MECHANICAL DATA



SO20

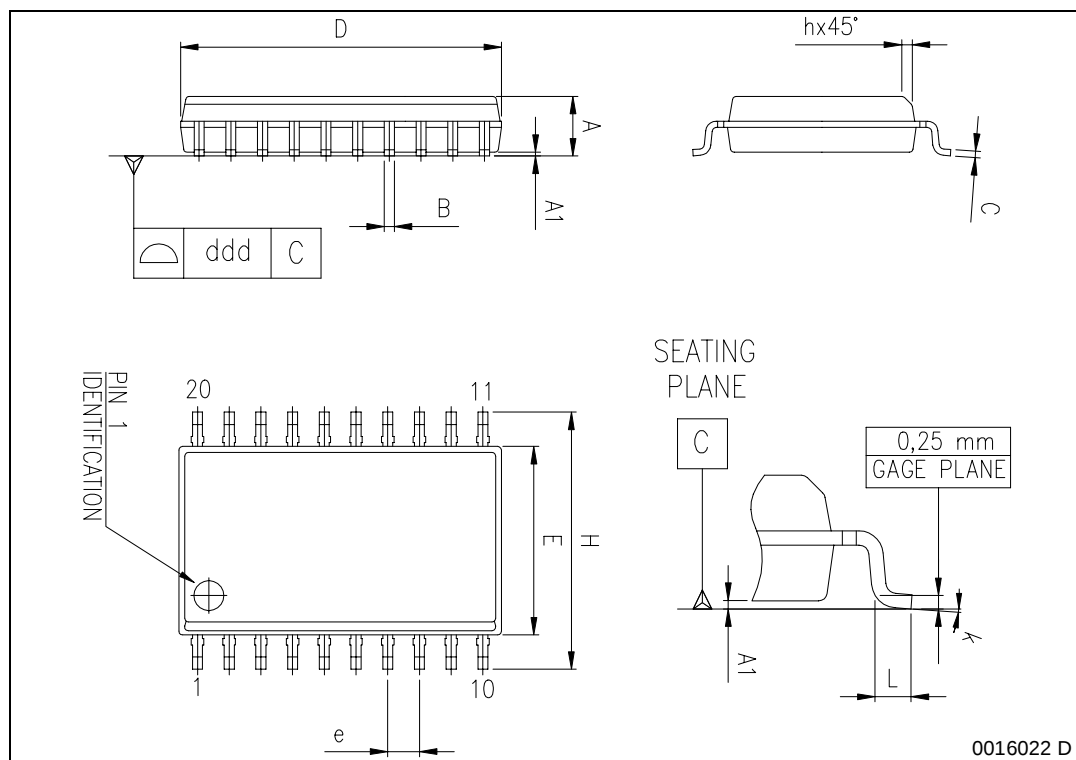


Table 6. Revision History

Date	Revision	Description of Changes
March 2004	2	Second Issue
May 2004	3	Stylesheet update. No content change

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